Title: 48v inverter IRF3710
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What voltage is irf3710?
IRF3710 MOSFET Datasheet: N-Ch,100V,57A. Full specification with pinout and replacement list The IRF3710 is an N-channel MOSFET designed for high-speed switching and low conduction loss. It features a 100V drain-source voltage,57A continuous current,low R DS (on) of 0.023?.

What is irf3710 MOSFET?
The IRF3710 is an N-channel MOSFETmanufactured by Infineon Technologies. It is designed for high-speed switching applications and offers low on-resistance,high current handling capabilities,and excellent thermal performance.

What is irf3710?
It features a 100V drain-source voltage, 57A continuous current, low R DS (on) of 0.023?. Optimized for power management, it excels in DC-DC converters, motor drives, automotive applications, offering high efficiency and thermal stability. Type Designator: IRF3710 Type of Transistor: MOSFET Type of Control Channel: N-Channel

How many pins does the irf3710 have?
The IRF3710 is typically available in a TO-220 package with three pins. The pin configuration is as follows: Gate Drive Voltage: Ensure the gate voltage (V GS) is within the recommended range (typically 10V for full enhancement). A gate resistor (e.g.,10?) can be used to limit inrush current and prevent damage to the gate.

IRF3710 is a N-channel power MOSFETs with VDS max: 100 V, RDS (on) max: 23 mOhm, Package: TO-220, Technology: IR MOSFET(TM), ID max: 57 A

View datasheets for IRF3710 (S,L)PbF by Infineon Technologies and other related components here.

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Learn how to use the IRF3710 with detailed documentation, including pinouts, usage guides, and example projects. Perfect for students, hobbyists, and developers integrating the IRF3710 into ...

Overall, the IRF3710 is a robust, efficient, and widely used N-channel MOSFET that provides a reliable solution for medium- to high-power switching applications where low loss and fast ...

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area.

This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and ...

Free download the datasheet for IRF3710 from OSEN.

Website: https://www.geochojnice.pl